

Title (en)

VERY HIGH CAPACITANCE FILM CAPACITOR AND METHOD FOR THE PRODUCTION OF SAME

Title (de)

SCHICHTKONDENSATOR MIT SEHR HOHER KAPAZITÄT UND VERFAHREN ZUR HERSTELLUNG DAVON

Title (fr)

CONDENSATEUR FILM A TRÈS HAUTE CAPACITÉ ET SON PROCÉDÉ DE FABRICATION

Publication

**EP 3520127 A1 20190807 (FR)**

Application

**EP 17771785 A 20170928**

Priority

- FR 1659489 A 20161003
- EP 2017074619 W 20170928

Abstract (en)

[origin: CA3036330A1] The present invention relates in particular to a very high capacitance film capacitor (1) that comprises a dielectric layer (100) consisting of at least one dielectric film (100a,..., 100i), each dielectric film (100a,..., 100i) of this dielectric layer (100) having the following parameters: - a relative dielectric permittivity [ef i] such that  $ef\ i = 10$ , - a thickness [ef i] such that  $0.05\ \mu\text{m} = ef\ i = 50\ \mu\text{m}$ , - a dielectric strength [Ef i] such that  $Ef\ i = 50\ \text{V}/\mu\text{m}$ , parameters in which "f" signifies "film" and i = 1, "i" designating the "ith" dielectric film (100i) of said dielectric layer (100), this dielectric layer (100) separating a first electronic charge carrier structure (200) from a second electronic charge carrier structure (300), these two structures having an opposite surface (S) separated by the dielectric layer(100).

IPC 8 full level

**H01G 4/30** (2006.01); **H01G 4/015** (2006.01); **H01G 4/06** (2006.01); **H01G 4/14** (2006.01); **H01G 4/32** (2006.01)

CPC (source: EP KR US)

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Citation (search report)

See references of WO 2018065289A1

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DOCDB simple family (publication)

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